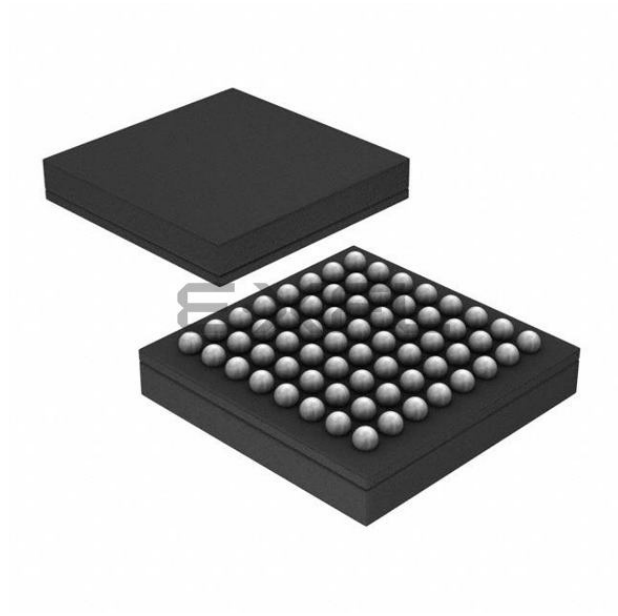

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 16x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TFBGA
Supplier Device Package	64-TFBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l053r6h6

3.19.5 Universal serial bus (USB)

The STM32L053x6/8 embed a full-speed USB device peripheral compliant with the USB specification version 2.0. The internal USB PHY supports USB FS signaling, embedded DP pull-up and also battery charging detection according to Battery Charging Specification Revision 1.2. The USB interface implements a full-speed (12 Mbit/s) function interface with added support for USB 2.0 Link Power Management. It has software-configurable endpoint setting with packet memory up to 1 KB and suspend/resume support. It requires a precise 48 MHz clock which can be generated from the internal main PLL (the clock source must use a HSE crystal oscillator) or by the internal 48 MHz oscillator in automatic trimming mode. The synchronization for this oscillator can be taken from the USB data stream itself (SOF signalization) which allows crystal-less operation.

3.20 Clock recovery system (CRS)

The STM32L053x6/8 embed a special block which allows automatic trimming of the internal 48 MHz oscillator to guarantee its optimal accuracy over the whole device operational range. This automatic trimming is based on the external synchronization signal, which could be either derived from USB SOF signalization, from LSE oscillator, from an external signal on CRS_SYNC pin or generated by user software. For faster lock-in during startup it is also possible to combine automatic trimming with manual trimming action.

3.21 Cyclic redundancy check (CRC) calculation unit

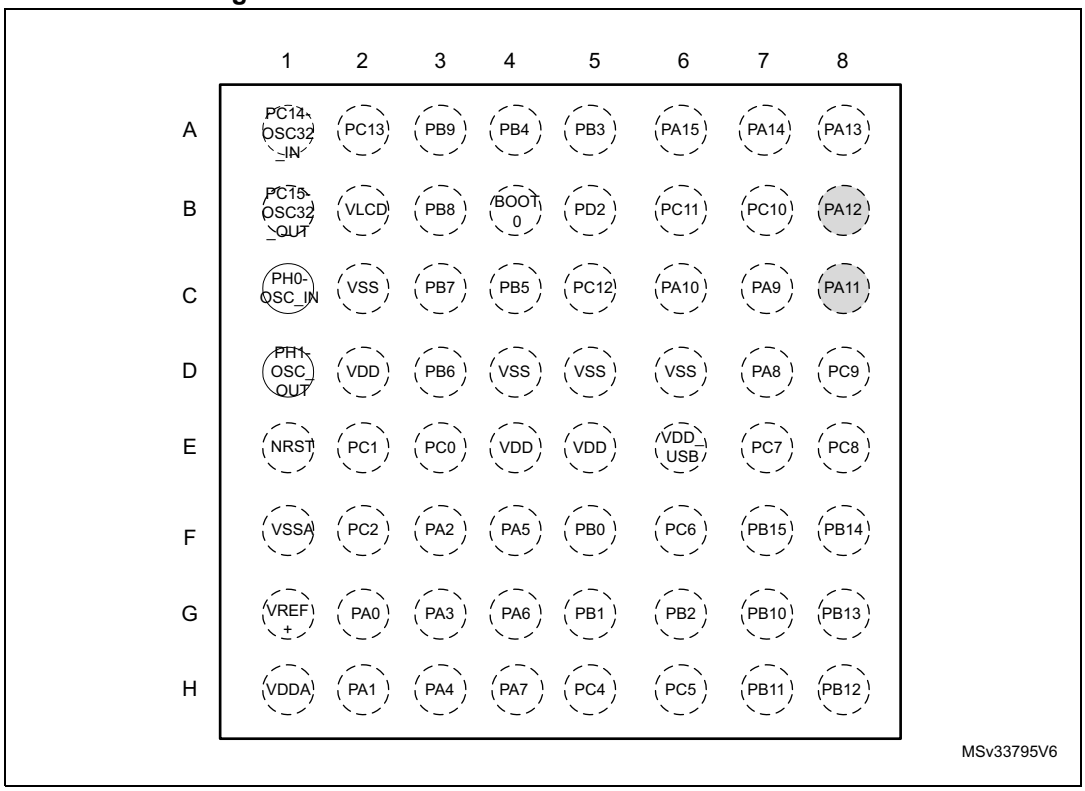
The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at linktime and stored at a given memory location.

3.22 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

Figure 4. STM32L053x6/8 TFBGA64 ballout - 5x 5 mm



1. The above figure shows the package top view.
2. I/O pin supplied by VDD_USB.

Table 14. Legend/abbreviations used in the pinout table (continued)

Name		Abbreviation	Definition
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers	
	Additional functions	Functions directly selected/enabled through peripheral registers	

Table 15. STM32L053x6/8 pin definitions

Pin number			Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP48	LQFP64	TFBGA64						
1	1	B2	VLCD	S	-	-	-	-
2	2	A2	PC13	I/O	FT	-	-	RTC_TAMP1/RTC_TS/RTC_OUT/WKUP2
3	3	A1	PC14-OSC32_IN (PC14)	I/O	FT	-	-	OSC32_IN
4	4	B1	PC15-OSC32_OUT (PC15)	I/O	TC	-	-	OSC32_OUT
5	5	C1	PH0-OSC_IN (PH0)	I/O	TC	-	USB_CRS_SYNC	OSC_IN
6	6	D1	PH1-OSC_OUT (PH1)	I/O	TC	-	-	OSC_OUT
7	7	E1	NRST	I/O	RST	-	-	-
-	8	E3	PC0	I/O	FT	-	LPTIM1_IN1, LCD_SEG18, EVENTOUT, TSC_G7_IO1	ADC_IN10
-	9	E2	PC1	I/O	FT	-	LPTIM1_OUT, LCD_SEG19, EVENTOUT, TSC_G7_IO2	ADC_IN11
-	10	F2	PC2	I/O	FT	-	LPTIM1_IN2, LCD_SEG20, SPI2_MISO/I2S2_MCK, TSC_G7_IO3	ADC_IN12
-	11	-	PC3	I/O	FT	-	LPTIM1_ETR, LCD_SEG21, SPI2_MOSI/I2S2_SD, TSC_G7_IO4	ADC_IN13

2. V_{DD_USB} must respect the following conditions:

- When V_{DD} is powered-on ($V_{DD} < V_{DD\_min}$), V_{DD_USB} should be always lower than V_{DD}.
- When V_{DD} is powered-down ($V_{DD} < V_{DD\_min}$), V_{DD_USB} should be always lower than V_{DD}.
- In operating mode, V_{DD_USB} could be lower or higher V_{DD}.
- If the USB is not used, V_{DD_USB} must range from V_{DD_min} to V_{DD_max} to be able to use PA11 and PA12 as standard I/Os.

3. To sustain a voltage higher than V_{DD}+0.3V, the internal pull-up/pull-down resistors must be disabled.
4. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see *Table 85: Thermal characteristics on page 123*).

Table 25. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	V
		Rising edge	3.08	3.15	3.20	
V_{hyst}	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterization results.
2. Valid for device version without BOR at power up. Please see option "D" in Ordering information scheme for more details.

6.3.3 Embedded internal reference voltage

The parameters given in *Table 27* are based on characterization results, unless otherwise specified.

Table 26. Embedded internal reference voltage calibration values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 25 °C V_{DDA}= 3 V	0x1FF8 0078 - 0x1FF8 0079

Table 27. Embedded internal reference voltage(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{REFINT\ out}$(2)	Internal reference voltage	– 40 °C < T_J < +125 °C	1.202	1.224	1.242	V
$T_{VREFINT}$	Internal reference startup time	-	-	2	3	ms
V_{VREF_MEAS}	V_{DDA} and V_{REF+} voltage during V_{REFINT} factory measure	-	2.99	3	3.01	V
A_{VREF_MEAS}	Accuracy of factory-measured V_{REFINT} value(3)	Including uncertainties due to ADC and V_{DDA}/V_{REF+} values	-	-	±5	mV
T_{Coeff}(4)	Temperature coefficient	–40 °C < T_J < +125 °C	-	25	100	ppm/°C
A_{Coeff}(4)	Long-term stability	1000 hours, T= 25 °C	-	-	1000	ppm
$V_{DDCoeff}$(4)	Voltage coefficient	3.0 V < V_{DDA} < 3.6 V	-	-	2000	ppm/V
$T_{S\_vrefint}$(4)(5)	ADC sampling time when reading the internal reference voltage	-	5	10	-	µs
T_{ADC_BUF}(4)	Startup time of reference voltage buffer for ADC	-	-	-	10	µs
I_{BUF_ADC}(4)	Consumption of reference voltage buffer for ADC	-	-	13.5	25	µA
I_{VREF_OUT}(4)	VREF_OUT output current(6)	-	-	-	1	µA
C_{VREF_OUT}(4)	VREF_OUT output load	-	-	-	50	pF

Figure 12. I_{DD} vs V_{DD}, at T_A= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE, 1WS

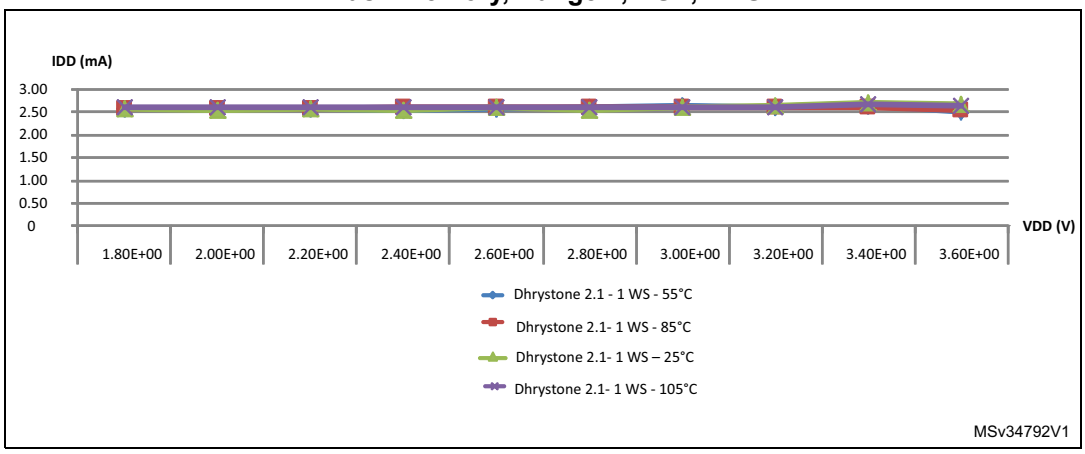


Figure 13. I_{DD} vs V_{DD}, at T_A= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSI16, 1WS

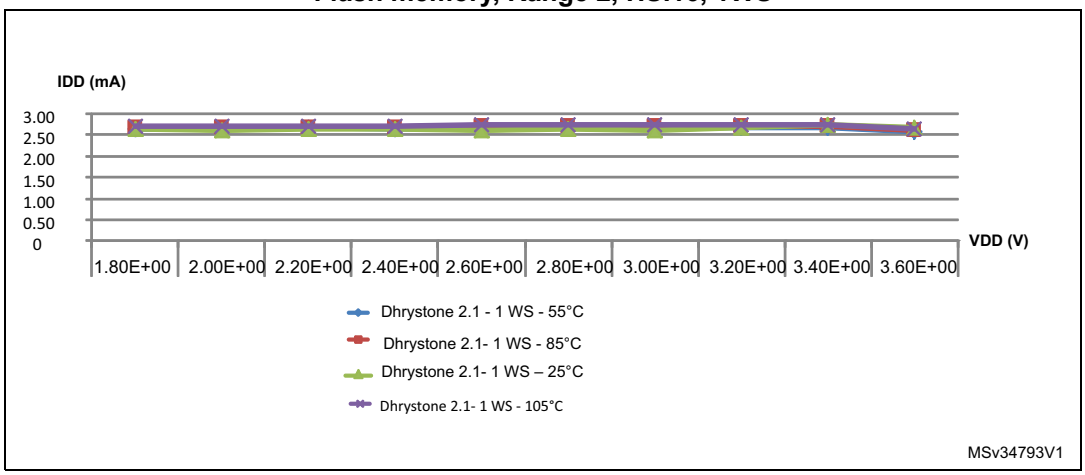


Table 32. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, Flash OFF	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	43.5	90	µA
				2 MHz	72	120	
				4 MHz	130	180	
			Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	4 MHz	160	210	
				8 MHz	305	370	
				16 MHz	590	710	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	370	430	
				16 MHz	715	860	
				32 MHz	1650	1900	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	18	65	
				524 kHz	31.5	75	
				4.2 MHz	140	210	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	665	830	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1750	2100	
	Supply current in Sleep mode, Flash ON	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	57.5	130	
				2 MHz	84	170	
				4 MHz	150	280	
			Range 2, CORE=1.5 V, VOS[1:0]=10	4 MHz	170	310	
				8 MHz	315	420	
				16 MHz	605	770	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	380	460	
				16 MHz	730	950	
				32 MHz	1650	2400	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	29.5	110	
				524 kHz	44.5	130	
				4.2 MHz	150	270	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	680	950	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1750	2100	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 54. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. f_{osc}/f_{CPU}			Unit
				8 MHz/ 4 MHz	8 MHz/ 16 MHz	8 MHz/ 32 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, compliant with IEC 61967-2	0.1 to 30 MHz	-21	-15	-12	dBµV
			30 to 130 MHz	-14	-12	-1	
			130 MHz to 1GHz	-10	-11	-7	
			EMI Level	1	1	1	-

6.3.13 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 58* are derived from tests performed under the conditions summarized in *Table 24*. All I/Os are CMOS and TTL compliant.

Table 58. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage	TC, FT, FTf, RST I/Os	-	-	$0.3V_{DD}$	V
		BOOT0 pin	-	-	$0.14V_{DD}$ (1)	
V_{IH}	Input high level voltage	All I/Os	$0.7\ V_{DD}$	-	-	
V_{hys}	I/O Schmitt trigger voltage hysteresis (2)	Standard I/Os	-	$10\%\ V_{DD}$ (3)	-	
		BOOT0 pin	-	0.01	-	
I_{lkg}	Input leakage current (4)	$V_{SS} \le V_{IN} \le V_{DD}$ All I/Os except for PA11, PA12, BOOT0 and FTf I/Os	-	-	±50	nA
		$V_{SS} \le V_{IN} \le V_{DD}$, PA11 and PA12 I/Os	-	-	-50/+250	
		$V_{SS} \le V_{IN} \le V_{DD}$ FTf I/Os	-	-	±100	
		$V_{DD} \le V_{IN} \le 5$ V All I/Os except for PA11, PA12, BOOT0 and FTf I/Os	-	-	200	nA
		$V_{DD} \le V_{IN} \le 5$ V FTf I/Os	-	-	500	
		$V_{DD} \le V_{IN} \le 5$ V PA11, PA12 and BOOT0	-	-	10	µA
R_{PU}	Weak pull-up equivalent resistor(5)	$V_{IN} = V_{SS}$	30	45	60	kΩ
R_{PD}	Weak pull-down equivalent resistor(5)	$V_{IN} = V_{DD}$	30	45	60	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Guaranteed by characterization.
2. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.
3. With a minimum of 200 mV. Guaranteed by characterization results.
4. The max. value may be exceeded if negative current is injected on adjacent pins.
5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This MOS/NMOS contribution to the series resistance is minimum (~10% order).

Output voltage levels

Unless otherwise specified, the parameters given in *Table 59* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24*. All I/Os are CMOS and TTL compliant.

Table 59. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL} (1)	Output low level voltage for an I/O pin	CMOS port(2), I_{IO} = +8 mA 2.7 V ≤ V_{DD} ≤ 3.6 V	-	0.4	V
V_{OH} (3)	Output high level voltage for an I/O pin		V_{DD}-0.4	-	
V_{OL} (1)	Output low level voltage for an I/O pin	TTL port(2), I_{IO} =+ 8 mA 2.7 V ≤V_{DD} ≤ 3.6 V	-	0.4	
V_{OH} (3)(4)	Output high level voltage for an I/O pin	TTL port(2), I_{IO} = -6 mA 2.7 V ≤V_{DD} ≤ 3.6 V	2.4	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = +15 mA 2.7 V ≤V_{DD} ≤ 3.6 V	-	1.3	
V_{OH} (3)(4)	Output high level voltage for an I/O pin	I_{IO} = -15 mA 2.7 V ≤V_{DD} ≤ 3.6 V	V_{DD}-1.3	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = +4 mA 1.65 V ≤V_{DD} < 3.6 V	-	0.45	
V_{OH} (3)(4)	Output high level voltage for an I/O pin	I_{IO} = -4 mA 1.65 V ≤V_{DD} ≤ 3.6 V	V_{DD}-0.45	-	
V_{OLFM+} (1)(4)	Output low level voltage for an FTf I/O pin in Fm+ mode	I_{IO} = 20 mA 2.7 V ≤V_{DD} ≤ 3.6 V	-	0.4	
		I_{IO} = 10 mA 1.65 V ≤V_{DD} ≤ 3.6 V	-	0.4	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 22*. The sum of the currents sunk by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 22*. The sum of the currents sourced by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
4. Guaranteed by characterization results.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 24* and *Table 60*, respectively.

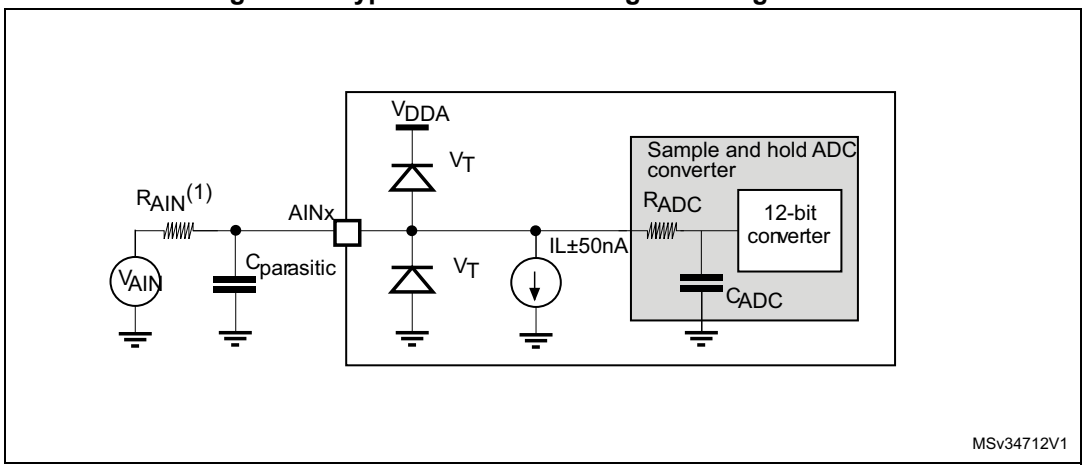
Unless otherwise specified, the parameters given in *Table 60* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 24*.

Table 60. I/O AC characteristics(1)

OSPEEDRx[1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Max(2)	Unit
00	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	400	kHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	100	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	125	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	320	
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	2	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	0.6	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	30	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	65	
10	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	10	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	2	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	13	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	28	
11	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	35	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	10	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	6	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	17	
Fm+ configuration(4)	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.5 V to 3.6 V	-	1	MHz
	$t_{f(IO)out}$	Output fall time		-	10	ns
	$t_{r(IO)out}$	Output rise time		-	30	
	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 1.65 V to 3.6 V	-	350	KHz
	$t_{f(IO)out}$	Output fall time		-	15	ns
	$t_{r(IO)out}$	Output rise time		-	60	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the line reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design.
3. The maximum frequency is defined in *Figure 24*.
4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the line reference manual for a detailed description of Fm+ I/O configuration.

Figure 27. Typical connection diagram using the ADC



1. Refer to *Table 62: ADC characteristics* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 28* or *Figure 29*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

Figure 28. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})

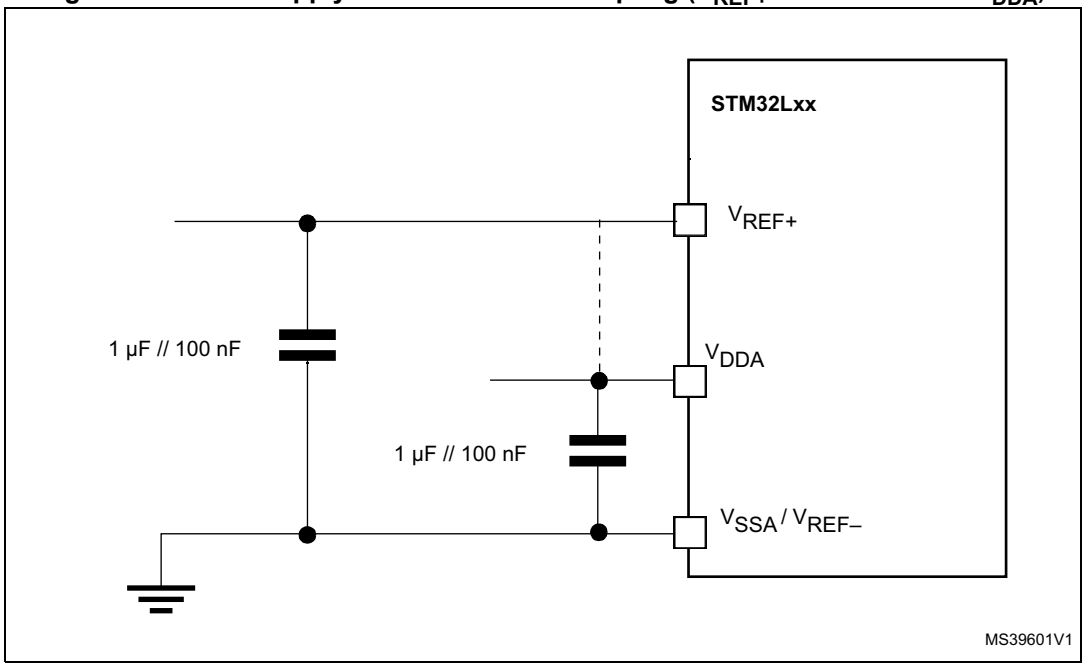
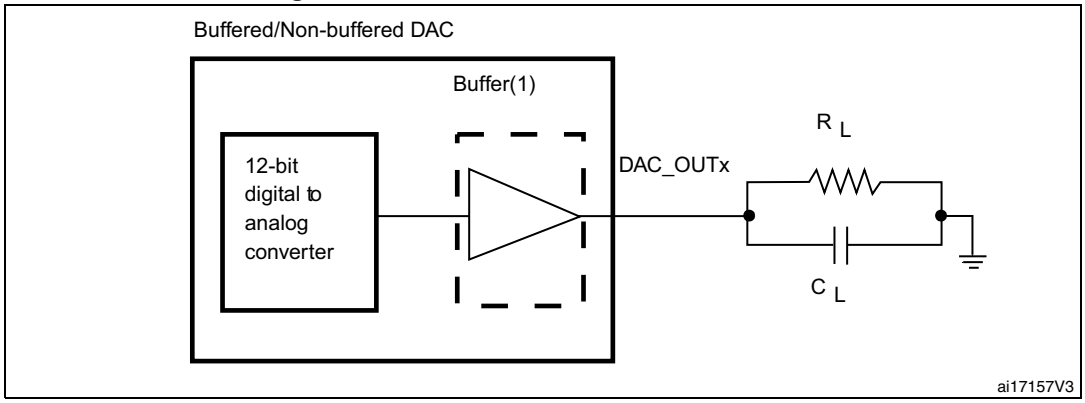


Table 65. DAC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{SETTLING}$	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes till DAC_OUT reaches final value ±1LSB	$C_L \leq 50$ pF, $R_L \geq 5$ kΩ	-	7	12	µs
Update rate	Max frequency for a correct DAC_OUT change (95% of final value) with 1 LSB variation in the input code	$C_L \leq 50$ pF, $R_L \geq 5$ kΩ	-	-	1	Msps
t_{WAKEUP}	Wakeup time from off state (setting the ENx bit in the DAC Control register)(9)	$C_L \leq 50$ pF, $R_L \geq 5$ kΩ	-	9	15	µs
PSRR+	V_{DDA} supply rejection ratio (static DC measurement)	$C_L \leq 50$ pF, $R_L \geq 5$ kΩ	-	-60	-35	dB

1. Guaranteed by characterization results.
2. Guaranteed by design, not tested in production.
3. Connected between DAC_OUT and V_{SSA}.
4. Difference between two consecutive codes - 1 LSB.
5. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095.
6. Difference between the value measured at Code (0x800) and the ideal value = $V_{REF+}/2$.
7. Difference between the value measured at Code (0x001) and the ideal value.
8. Difference between ideal slope of the transfer function and measured slope computed from code 0x000 and 0xFFF when buffer is OFF, and from code giving 0.2 V and (V_{DDA} – 0.2) V when buffer is ON.
9. In buffered mode, the output can overshoot above the final value for low input code (starting from min value).

Figure 30. 12-bit buffered/non-buffered DAC



6.3.19 Timer characteristics

TIM timer characteristics

The parameters given in the *Table 70* are guaranteed by design.

Refer to *Section 6.3.13: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 70. TIMx characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time		1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 32 MHz	31.25	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4		0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK}$ = 32 MHz	0	16	MHz
Res_{TIM}	Timer resolution	-		16	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected (timer's prescaler disabled)	-	1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 32 MHz	0.0312	2048	µs
t_{MAX_COUNT}	Maximum possible count	-	-	65536 × 65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 32 MHz	-	134.2	s

1. TIMx is used as a general term to refer to the TIM2, TIM6, TIM21, and TIM22 timers.

6.3.20 Communications interfaces

I^2C interface characteristics

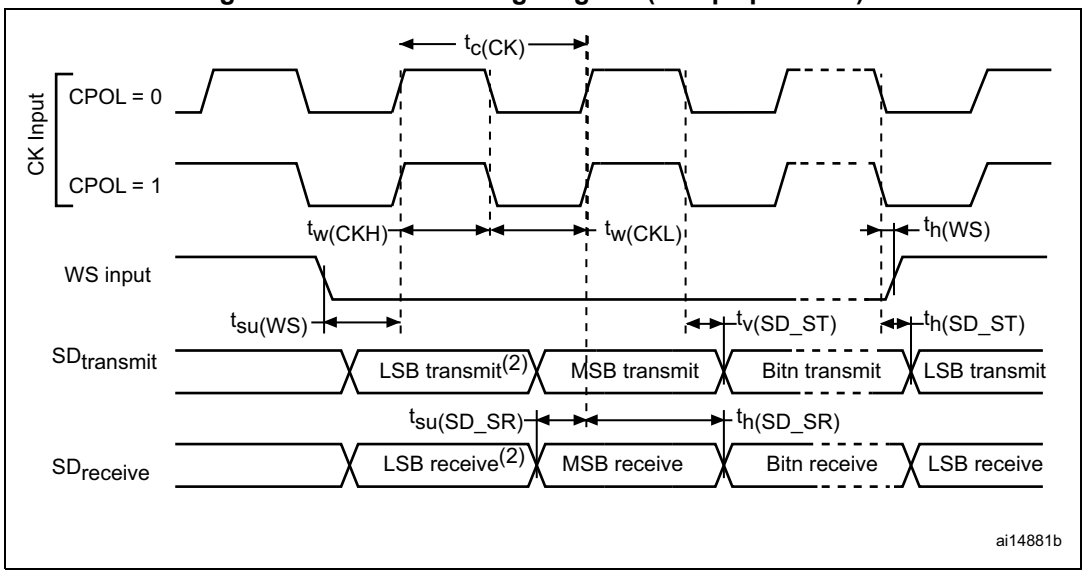
The I^2C interface meets the timings requirements of the I^2C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm) : with a bit rate up to 100 kbit/s
- Fast-mode (Fm) : with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+) : with a bit rate up to 1 Mbit/s.

The I^2C timing requirements are guaranteed by design when the I^2C peripheral is properly configured (refer to the reference manual for details). The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and VDDIOx is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement (refer to *Section 6.3.13: I/O port characteristics* for the I2C I/Os characteristics).

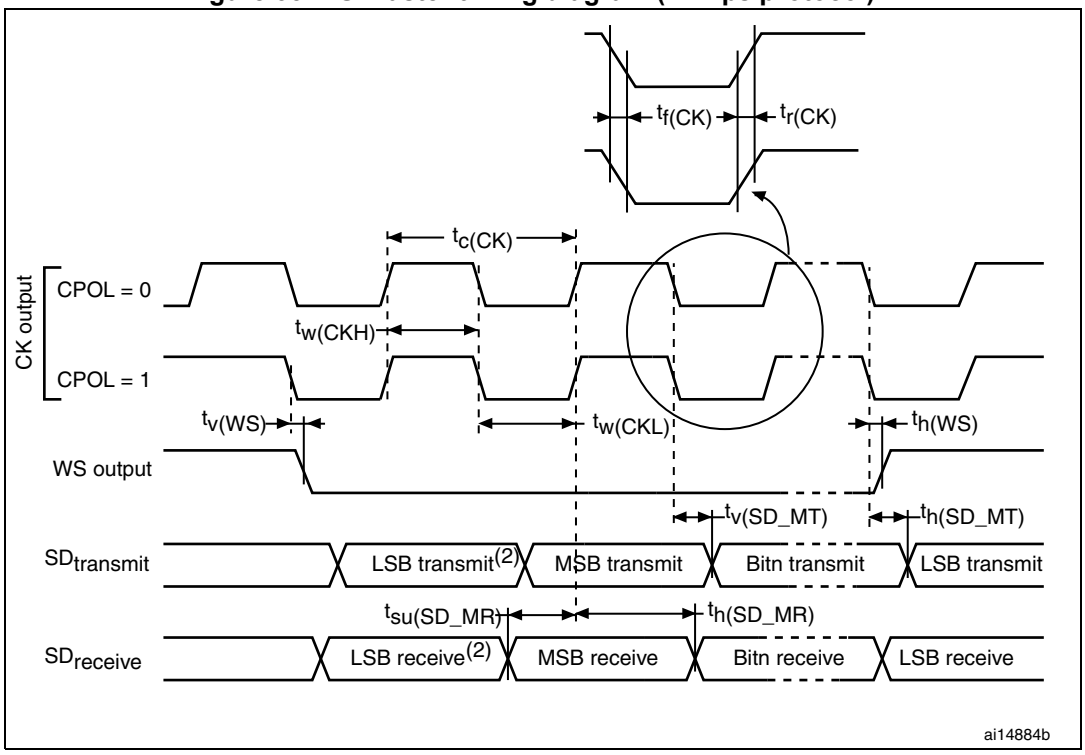
All I^2C SDA and SCL I/Os embed an analog filter (see *Table 71* for the analog filter characteristics).

Figure 34. I²S slave timing diagram (Philips protocol)(1)



1. Measurement points are done at CMOS levels: $0.3 \times V_{DD}$ and $0.7 \times V_{DD}$.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 35. I²S master timing diagram (Philips protocol)(1)



1. Guaranteed by characterization results.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 36. USB timings: definition of data signal rise and fall time

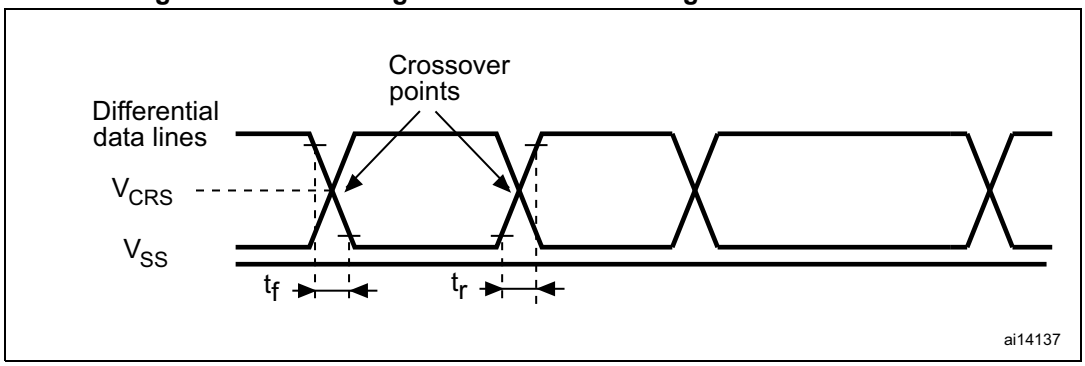


Table 79. USB: full speed electrical characteristics

Driver characteristics[1]					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
t_r	Rise time[2]	C_L = 50 pF	4	20	ns
t_f	Fall Time[2]	C_L = 50 pF	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

6.3.21 LCD controller

The devices embed a built-in step-up converter to provide a constant LCD reference voltage independently from the V_{DD} voltage. An external capacitor C_{ext} must be connected to the V_{LCD} pin to decouple this converter.

Table 80. LCD controller characteristics

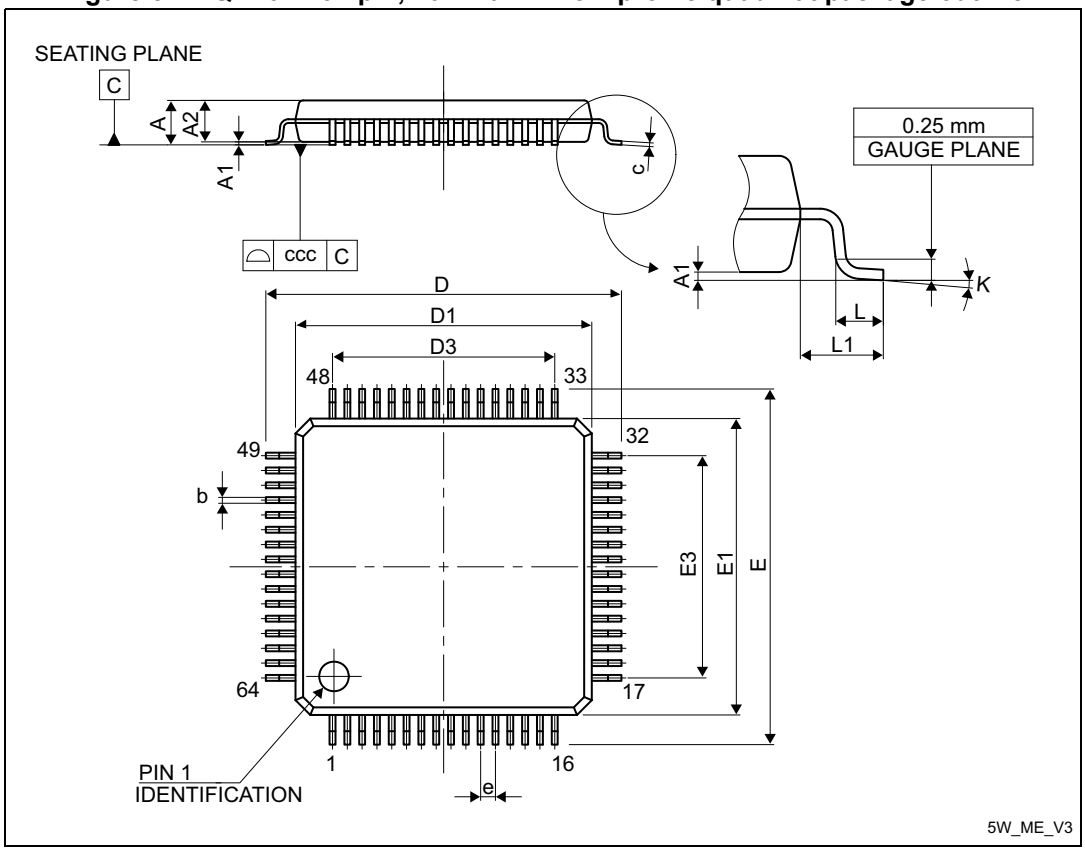
Symbol	Parameter	Min	Typ	Max	Unit
V_{LCD}	LCD external voltage	-	-	3.6	V
V_{LCD0}	LCD internal reference voltage 0	-	2.6	-	
V_{LCD1}	LCD internal reference voltage 1	-	2.73	-	
V_{LCD2}	LCD internal reference voltage 2	-	2.86	-	
V_{LCD3}	LCD internal reference voltage 3	-	2.98	-	
V_{LCD4}	LCD internal reference voltage 4	-	3.12	-	
V_{LCD5}	LCD internal reference voltage 5	-	3.26	-	
V_{LCD6}	LCD internal reference voltage 6	-	3.4	-	
V_{LCD7}	LCD internal reference voltage 7	-	3.55	-	
C_{ext}	V_{LCD} external capacitance	0.1	-	2	µF

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status *are available at www.st.com.* ECOPACK® is an ST trademark.

7.1 LQFP64 package information

Figure 37. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 87. Document revision history (continued)

Date	Revision	Changes
11-Mar-2016	6	Updated number of SPIs on cover page and in *Table 1: Ultra-low-power STM32L053x6/x8 device features and peripheral counts*. Changed minimum comparator supply voltage to 1.65 V on cover page. Added number of fast and standard channels in *Section 3.12: Analog-to-digital converter (ADC)*. Changed LCD_VLCD1 into LCD_VLCD2 in *Section 3.13.2: VLCD voltage monitoring*. Updated *Section 3.19.2: Universal synchronous/asynchronous receiver transmitter (USART)* and *Section 3.19.4: Serial peripheral interface (SPI)/Inter-integrated sound (I2S)* to mention the fact that USARTs with synchronous mode feature can be used as SPI master interfaces. Added baudrate allowing to wake up the MCU from Stop mode in *Section 3.19.2: Universal synchronous/asynchronous receiver transmitter (USART)* and *Section 3.19.3: Low-power universal asynchronous receiver transmitter (LPUART)*. In *Section 6: Electrical characteristics*, updated notes related to values guaranteed by characterization. *Section 6.3.15: 12-bit ADC characteristics*: – *Table 62: ADC characteristics*: Distinction made between V_{DDA} for fast and standard channels; added note 1 Added note 4 related to R_{ADC}. Updated f_{TRIG} and V_{AIN} maximum value; added V_{REF+}. Updated t_S and t_{CONV}. – Updated equation 1 description. – Updated *Table 63: RAIN max for fADC = 16 MHz* for f_{ADC} = 16 MHz and distinction made between fast and standard channels. Updated R_O and added Note 2 in *Table 65: DAC characteristics*. Added *Table 72: USART/LPUART characteristics*. Updated *Figure 45: LQFP48 marking example (package top view)*.

Table 87. Document revision history (continued)

Date	Revision	Changes
11-Oct-2016	7	Updated note related to PA4 in *Table 15: STM32L053x6/8 pin definitions*; added same note to PA4 in *Table 8: Capacitive sensing GPIOs available on STM32L053x6/8 devices* and *Table 16: Alternate function port A*. Updated VDD_USB and VDD in *Table 15: STM32L053x6/8 pin definitions*. Renamed USB_OE into USB_NOE. Added mission profile compliance with JEDEC JESD47 in *Section 6.2: Absolute maximum ratings*. Added note 2. related to the position of the 0.1 µF capacitor below *Figure 25: Recommended NRST pin protection*. Updated R_L in *Table 62: ADC characteristics*. Updated t_{AF} maximum value for range 1 in *Table 71: I2C analog filter characteristics*. Updated $t_{WUUSART}$ description in *Table 72: USART/LPUART characteristics*. Updated *Figure 31: SPI timing diagram - slave mode and CPHA = 0* and *Figure 32: SPI timing diagram - slave mode and CPHA = 1(1)*. Added reference to optional marking or inset/upset marks in all package device marking sections.